

Amendments to the Specification:

Please replace the paragraphs beginning at page 52, line 2, with the following amended paragraphs:

The image signal driver circuit 606 comprises a shift ~~resister register~~ circuit 501a, a level shifter circuit 502a, a buffer circuit 503a, and a sampling circuit 504. In addition, the scanning signal driver circuits (A) and (B) 185 comprises a shift ~~resister register~~ circuit 501b, a level shifter circuit 502b, and a buffer circuit 503b.

The driving voltages of the shift ~~resister register~~ circuits 501a and 501b are between 5 and 16V (typically 10V). A TFT of a CMOS circuit for forming this circuit is formed of the first p-channel TFT 200 and the first n-channel TFT 201 of Fig. 5B, or the TFT may be formed of the first p-channel TFT 280 and the first n-channel TFT 281 shown in Fig. 9A. In addition, since the driving voltage of the level shifter circuits 502a and 502b and the buffer circuits 503a and 503b become as high as 14 to 16V, it is preferable that the TFT structure be formed into a multi-gate structure as shown in Fig. 9A. Forming the TFT into a multi-gate structure is effective in raising voltage-resistance and improving the reliability of the circuits.